

contd
B1 wherein the dummy diffused layer has its surface covered with an anti-silicidation film at least partially, on which no gate electrode is provided.

14. (Amended) A semiconductor device comprising:
a substrate;
a source/drain diffused layer formed in the substrate for a transistor; and
a dummy diffused layer formed in the substrate,
wherein the source/drain diffused layer has its surface silicided, and
wherein the dummy diffused layer has its surface covered with an anti-silicidation film at least partially, and
wherein the dummy diffused layer is located between an analog circuit block and
B2 a digital circuit block.

15. (Amended) A semiconductor device comprising:
a substrate;
a source/drain diffused layer formed in the substrate for a transistor; and
a dummy diffused layer formed in the substrate,
wherein the source/drain diffused layer has its surface silicided, and
wherein the dummy diffused layer has its surface covered with an anti-silicidation film at least partially, and
wherein the dummy diffused layer is not electrically coupled to another component via an interconnect.